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フェニテックセミコンダクター株式会社

RDPxxx

Transient Voltage Suppressor

Features

- Suitable to small packages (SOD-923) Chip Size=0.26mmsq
- High ESD protection level IEC61000-4-2(ESD) +/-30Kv(Contact)
  +/-30Kv(Air)

Application

- Cellular phones audio
- MP3 players
- Digital cameras
- Portable applications
- Mobile telephone

Item	Characteristics
Wafer size	5inch
Chip size	260*260um

Maximum Ratings (Ta=25degC)

Symbol	Parameter	Value	Units
Ppk	Peak Power Dissipation @tp=8/20us (*1) RDP5V0 RDP6V2	 86 92	 W W
Pd	Power Dissipation(*1)	150	mW
T_{stg}	Storage Temperature Range	-55 to+150	Deg C
T_j	Maximum junction temperature (*1)	150	Deg C
V_{pp}	Electrostatic discharge IEC61000-4-2 air discharge (*1)(*2) IEC61000-4-2 contact discharge (*1)	 ±30 ±30	 kV kV

(*1) Rating value for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic), mounted on PCB of 1.5cm by 2.5cm.

(*2)Reference only

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Electrical Characteristics (Ta=25degC)

Ratings at 25degC ambient temperature unless otherwise specified.

Device	V_{RWM} (V) Max	I_R @ V_{RWM} (uA) Max	V_{BR} @1mA (V) Min	V_F @10mA (V) Max	Vc *1 @Ipp (V) Max	Ipp *1 (A) Max	C *2 @0V (pF) Typ
RDP5V0	3.3	2.5	5.0	0.9	12.3	7.0	45
RDP6V2	5.0	1.0	6.2	0.9	13.2	7.0	40

*1 Package=SOT-23 (front: Au wire 35um, back: Au eutectic) @tp=8/20us

*2 @f=1MHz

Ordering Inforomation

Type	Chip Thickness	Back Metalization	Die Bonding For
RDP5V0J	100um	Au	Eutectic
RDP6V2J	100um	Au	Eutectic

Note